

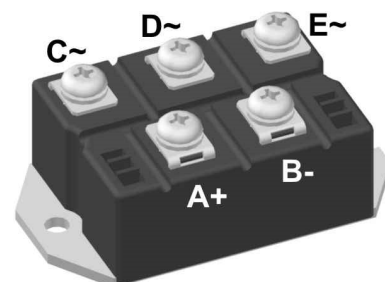
Standard Rectifier Module

3~ Rectifier	
V_{RRM}	= 800 V
I_{DAV}	= 125 A
I_{FSM}	= 1200 A

3~ Rectifier Bridge

Part number

VUO110-08NO7



 E72873



Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

Applications:

- Diode for main rectification
- For three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Package: PWS-E

- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Easy to mount with two screws
- Base plate: Copper internally DCB isolated
- Advanced power cycling

Disclaimer Notice

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Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				900	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				800	V
I_R	reverse current	$V_R = 800\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			100	μA
		$V_R = 800\text{ V}$	$T_{VJ} = 150^{\circ}\text{C}$			2	mA
V_F	forward voltage drop	$I_F = 50\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			1.13	V
		$I_F = 150\text{ A}$				1.46	V
		$I_F = 50\text{ A}$	$T_{VJ} = 125^{\circ}\text{C}$			1.04	V
		$I_F = 150\text{ A}$				1.47	V
I_{DAV}	bridge output current	$T_C = 110^{\circ}\text{C}$ rectangular	$T_{VJ} = 150^{\circ}\text{C}$ $d = \frac{1}{3}$			125	A
V_{F0}	threshold voltage	} for power loss calculation only		$T_{VJ} = 150^{\circ}\text{C}$		0.79	V
r_F	slope resistance					4.5	m Ω
R_{thJC}	thermal resistance junction to case					0.7	K/W
R_{thCH}	thermal resistance case to heatsink				0.3		K/W
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$				175	W
I_{FSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			1.20	kA
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			1.30	kA
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}\text{C}$			1.02	kA
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			1.10	kA
I^2t	value for fusing	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			7.20	kA ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			6.98	kA ² s
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}\text{C}$			5.20	kA ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			5.04	kA ² s
C_J	junction capacitance	$V_R = 400\text{ V}; f = 1\text{ MHz}$			37		pF

Package PWS-E				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
I _{RMS}	RMS current	per terminal			200	A	
T _{VJ}	virtual junction temperature		-40		150	°C	
T _{op}	operation temperature		-40		125	°C	
T _{stg}	storage temperature		-40		125	°C	
Weight				284		g	
M _D	mounting torque		4.25		5.75	Nm	
M _T	terminal torque		4.25		5.75	Nm	
d _{Spp/App}	creepage distance on surface striking distance through air	terminal to terminal	12.0			mm	
d _{Spb/Apb}		terminal to backside	26.0			mm	
V _{ISOL}	isolation voltage	t = 1 second	3000			V	
		t = 1 minute	2500			V	
			50/60 Hz, RMS; I _{ISOL} ≤ 1 mA				



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	VUO110-08NO7	VUO110-08NO7	Box	5	462365

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 150^{\circ}\text{C}$



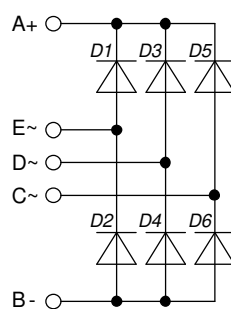
Rectifier

$V_{0\max}$ threshold voltage 0.79

V

$R_{0\max}$ slope resistance * 3.3

mΩ



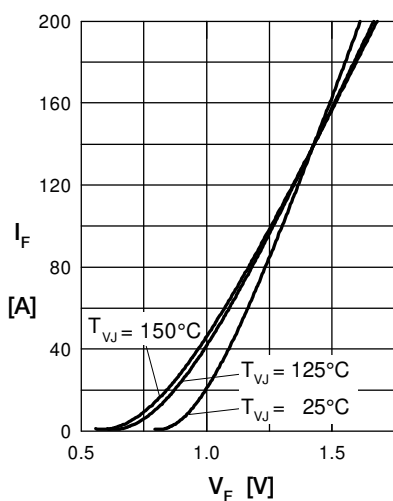
Rectifier


Fig. 1 Forward current vs. voltage drop per diode

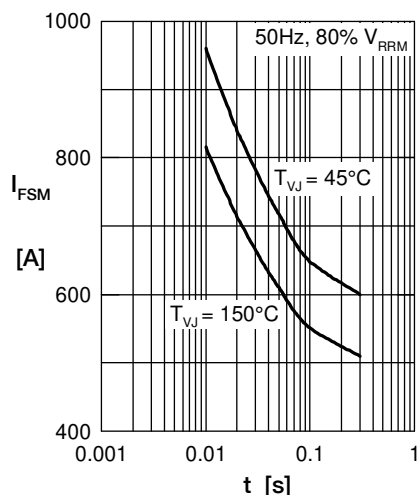


Fig. 2 Surge overload current vs. time per diode

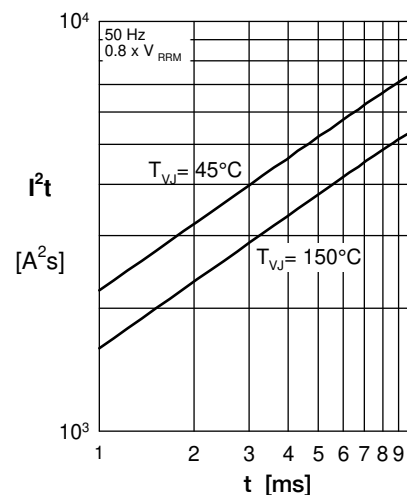


Fig. 3 I^2t vs. time per diode

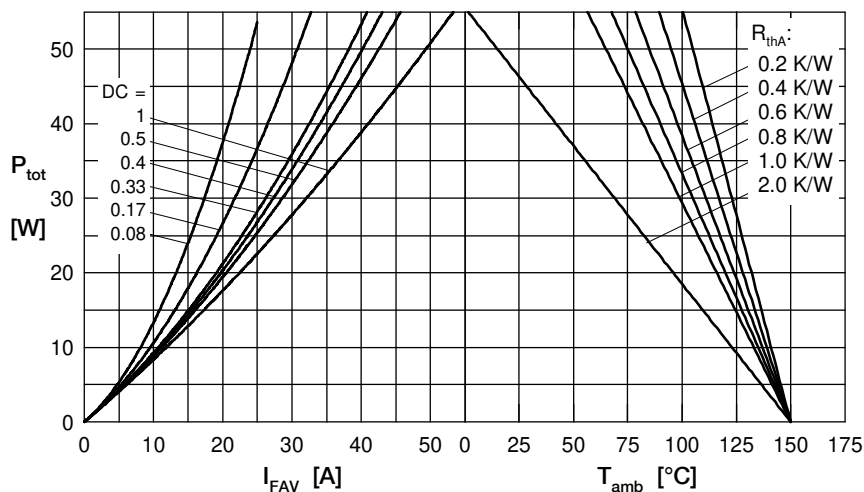


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

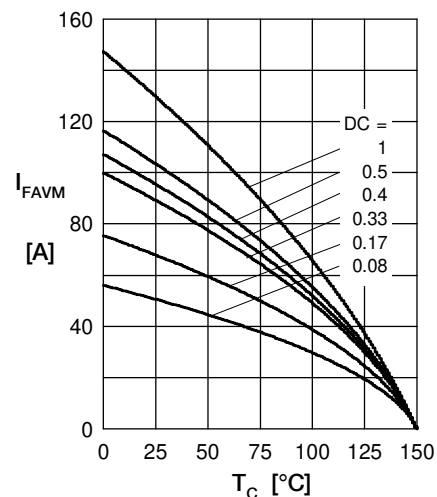


Fig. 5 Max. forward current vs. case temperature per diode

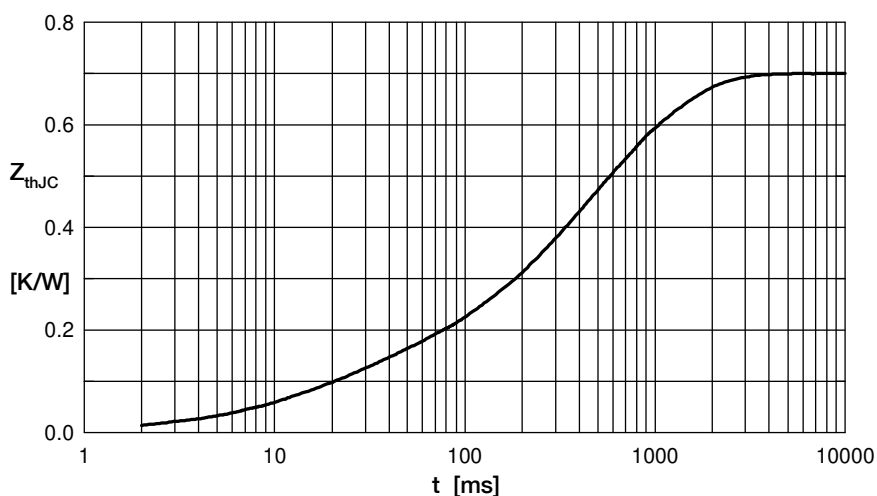


Fig. 6 Transient thermal impedance junction to case vs. time per diode

R_i	t_i
0.100	0.020
0.010	0.010
0.162	0.225
0.258	0.800
0.170	0.580